



# COLLEGE OF ENGINEERING & TECHNOLOGY

Department: Electronics and Communications Engineering

Lecturer: Dr. Mostafa Fedawy.

Course Title: Electronic Devices I

Course Code: EC 233

Cairo Branch

## Sheet 3

### I. Indicate whether each of the following statements is true or false (give reasons):

- 1- The density of states at the top of the valence band is greater than zero.
- 2- The density of states in the valence band increases with increasing electron energy.
- 3- In an n-type semiconductor, the Fermi level moves closer to the middle of the energy gap as the temperature increases.
- 4- For temperatures greater than zero, the probability that an electron may occupy an allowed state at the Fermi level is dependent on temperature.
- 5- For semiconductors, the area under the energy distribution curve for the conduction band represents the total number of free electrons per cubic meter at a certain temperature.
- 6- The mass action law ( $np = n_i^2$ ) is valid at thermal equilibrium in intrinsic semiconductor only.

### II. Choose the correct answer justifying your choice:

- 1- If the density of available quantum states is  $G$  at an energy level  $0.01$  eV above the bottom of the edge of conduction band, this density will be ..... at an energy level  $0.04$  eV above the bottom of the edge of conduction band.  
(a)  $0.0016 G$       (b)  $4 G$       (c)  $0.2 G$       (d)  $2 G$       (e)  $0.02 G$
- 2- The density of available quantum states for electrons at an energy  $\Delta E$  above the bottom of the conduction band is ..... that for holes at an energy  $\Delta E$  below the top of the edge of valence band in silicon  
(a) higher than    (b) less than    (c) equal to    (d) not related to
- 3- If  $E_F$  is the fermi energy, the probability that the the level  $E_f + E$  is empty is ..... the probability that the level  $E_f - E$  is occupied  
(a) higher than    (b) less than    (c) equal to    (d) not related to

### III. Solve the following problems:

- 1- Determine the total number of energy states in GaAs between  $E_c$  and  $E_c + kT$  at  $T = 300$  K.
- 2- (a) Determine the probability that an energy level is occupied by an electron if the state is above the fermi level by (i)  $kT$  , (ii)  $5kT$  , (iii)  $10kT$ .

(b) Determine the probability that an energy level is empty of an electron if the state is below the Fermi level by (i)  $kT$ , (ii)  $5kT$ , (iii)  $10kT$ .

- 3- Calculate the temperature at which there is a  $10^{-6}$  probability that an energy state  $0.55 \text{ eV}$  above the Fermi energy level is occupied by an electron.
- 4- Calculate the energy relative to the Fermi energy for which the Fermi function equals 5%. Write the answer in units of  $kT$ .

**Good Luck 😊**